

Amendments to the Claims:

Claims 23-26, 29-31, and 34-42 have been amended herein. Please note that all claims currently pending and under consideration in the referenced application are shown below. Please enter these claims as amended. This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

Claims 1 through 22 (Cancelled)

23. (Currently amended) ~~An operable~~A gate stack, including stack comprising a non-crystalline metallic silicide film, wherein the gate stack is operable.

24. (Currently amended) ~~An operable~~A gate stack, including- stack comprising an amorphous metallic silicide film, wherein the amorphous metallic silicide film is substantially devoid of silicon clusters and wherein the gate stack is operable.

25. (Currently amended) ~~An operable~~A gate stack on a silicon substrate having a dielectric layer thereover, the dielectric layer being substantially devoid of pitting, the operable gate stack comprising:
a polysilicon layer disposed over the dielectric layer;
a non-crystalline metallic silicide film disposed over the polysilicon layer; and
a dielectric cap on the non-crystalline metallic silicide film,
wherein the gate stack is operable.

26. (Currently amended) A gate stack structure comprising ~~an operable~~a gate stack on a dielectric layer, over a silicon substrate, wherein the dielectric layer is substantially devoid of pitting, ~~the operable~~wherein the gate stack is operable and comprising comprises an amorphous metallic silicide film which is substantially devoid of silicon clusters.

Claims 27 and 28 (Cancelled)

29. (Currently amended) A semiconductor device, comprising at least one operable gate stack ~~including~~ comprising a non-crystalline metallic silicide film.

30. (Currently amended) The semiconductor device of claim 29, wherein the at least one operable gate stack further ~~includes~~ comprises a silicon substrate having a dielectric layer thereover, the dielectric layer being substantially devoid of pitting, and a polysilicon layer disposed over the dielectric layer, wherein the non-crystalline metallic silicide film is disposed over the polysilicon layer.

31. (Currently amended) A semiconductor ~~device,~~ device comprising at least one operable gate stack structure on a dielectric layer, over a silicon substrate, wherein the dielectric layer is substantially devoid of pitting, and wherein the at least one operable gate stack structure ~~including~~ comprises an amorphous metallic silicide film which is substantially devoid of silicon clusters.

Claims 32 and 33 (Cancelled)

34. (Currently amended) The ~~operable~~ gate stack of claim 23, wherein the ~~operable~~ gate stack is formed on a silicon substrate having a dielectric layer thereover, the dielectric layer being substantially devoid of pitting.

35. (Currently amended) The ~~operable~~ gate stack of claim 34, further comprising a dielectric cap on the non-crystalline metallic silicide film.

36. (Currently amended) The ~~operable~~ gate stack of claim 35, wherein the dielectric cap comprises at least one of silicon nitride and silicon dioxide.

37. (Currently amended) The ~~operable~~ gate stack of claim 24, wherein the ~~operable~~ gate stack is formed on a silicon substrate having a dielectric layer thereover, the dielectric layer being substantially devoid of pitting.

38. (Currently amended) The ~~operable~~ gate stack of claim 37, further comprising a dielectric cap on the amorphous metallic silicide film.

39. (Currently amended) The ~~operable~~ gate stack of claim 38, wherein the dielectric cap comprises at least one of silicon nitride and silicon dioxide.

40. (Currently amended) The ~~operable~~ gate stack of claim 25, wherein the dielectric cap comprises at least one of silicon nitride and silicon dioxide.

41. (Currently amended) The ~~operable~~ gate stack of claim 26, further comprising a dielectric cap on the amorphous metallic silicide film.

42. (Currently amended) The ~~operable~~ gate stack of ~~claim 43~~ claim 41, wherein the dielectric cap comprises at least one of silicon nitride and silicon dioxide.

43. (Previously presented) The semiconductor device of claim 29, wherein the at least one operable gate stack further comprises a dielectric cap on the non-crystalline metallic silicide film.

44. (Previously presented) The semiconductor device of claim 43, wherein the dielectric cap comprises at least one of silicon nitride and silicon dioxide.